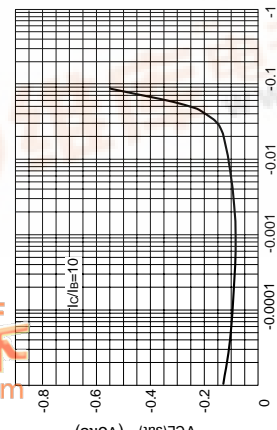


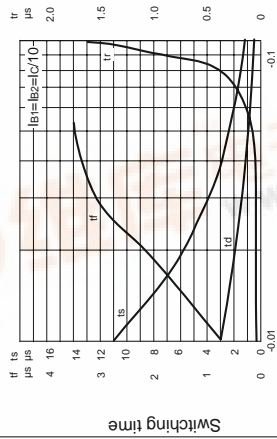
ZTX556 ZTX557

TYPICAL CHARACTERISTICS



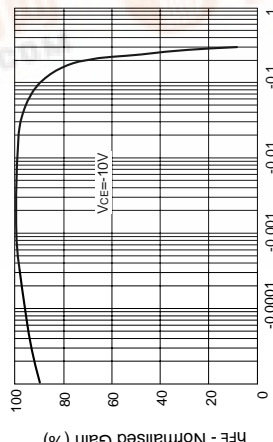
IC - Collector Current (Amps)

VCE(sat) v IC



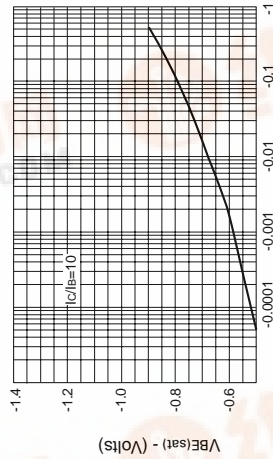
IC - Collector Current (Amps)

Switching Speeds



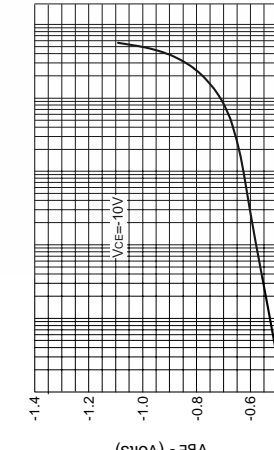
IC - Collector Current (Amps)

hFE v IC



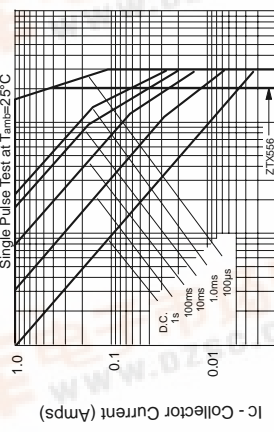
IC - Collector Current (Amps)

VBE(sat) v IC



IC - Collector Current (Amps)

VBE(on) v IC



IC - Collector Current (Amps)

Safe Operating Area

PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTORS

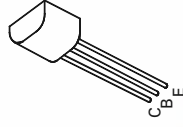
ISSUE 1 - JULY 94

FEATURES

- * 300 Volt V_{CEO}
- * 0.5 Amp continuous current
- * P_{tot} = 1 Watt

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	ZTX556	ZTX557	UNIT
Collector-Base Voltage	V _{CBO}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-1	A
Continuous Collector Current	I _C	-0.5	A
Power Dissipation	P _{tot}	1.0	W
Operating and Storage Temperature Range	T _j ; T _{stg}	-55 to +200	°C



E-Line
TO92 Compatible

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

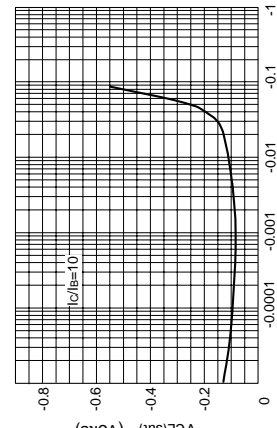
PARAMETER	SYMBOL	ZTX556		ZTX557		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-200		-300		V	I _C = -100µA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-200		-300		V	I _C = -10mA*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5		-5		V	I _E = -100µA
Collector Cut-Off Current	I _{CBO}	-0.1		-0.1		µA	V _{CB} = -160V V _{CB} = -200V
Emitter Cut-Off Current	I _{EBO}	-0.1		-0.1		µA	V _{EB} = -4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-0.3		-0.3		V	I _C = -50mA, I _B = -5mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}	-1		-1		V	I _C = -50mA, I _B = -5mA*
Base-Emitter Turn-on Voltage	V _{BE(on)}	-1		-1		V	I _C = -50mA, V _{CE} = -10V*
Static Forward Current Transfer Ratio	h _{FE}	50	300	50	300		I _C = -10mA, V _{CE} = -10V* I _C = -50mA, V _{CE} = -10V*
Transition Frequency	f _T	75		75		MHz	I _C = -50mA, V _{CE} = -10V f = 100MHz

查询ZTX556供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

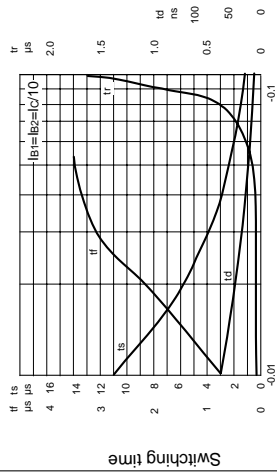
ZTX556 ZTX557

TYPICAL CHARACTERISTICS



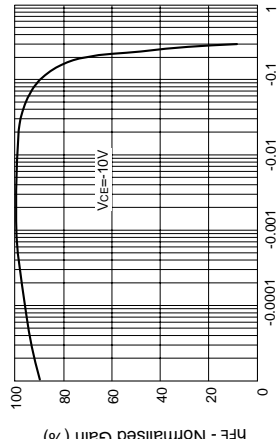
IC - Collector Current (Amps)

VCE(sat) v IC



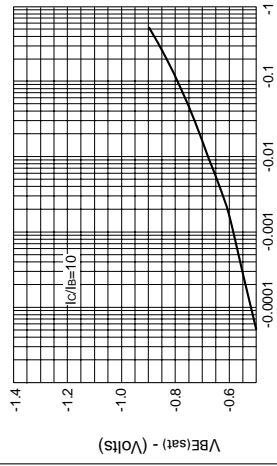
IC - Collector Current (Amps)

Switching Speeds



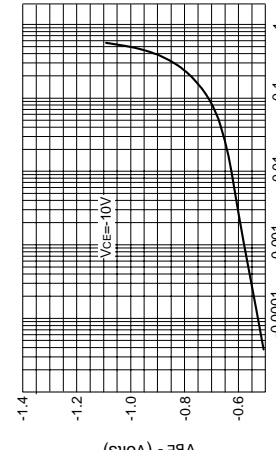
IC - Collector Current (Amps)

hFE v IC



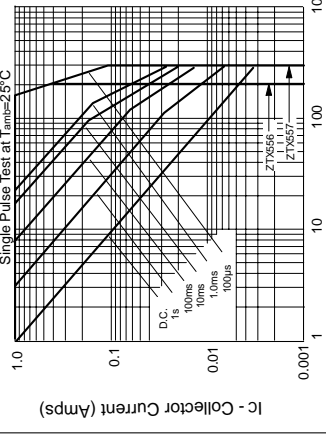
IC - Collector Current (Amps)

VBE(sat) v IC



IC - Collector Current (Amps)

VBE(on) v IC



IC - Collector Current (Amps)

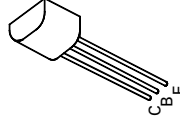
Safe Operating Area

PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTORS

ISSUE 1 - JULY 94

FEATURES

- * 300 Volt V_{CEO}
- * 0.5 Amp continuous current
- * $P_{tot} = 1$ Watt



E-Line

TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX556	ZTX557	UNIT
Collector-Base Voltage	V_{CBO}	-200	-300	V
Collector-Emitter Voltage	V_{CEO}	-200	-300	V
Emitter-Base Voltage	V_{EBO}	-5	-5	V
Peak Pulse Current	I_{CM}	-1	-1	A
Continuous Collector Current	I_C	-0.5	-0.5	A
Power Dissipation	P_{tot}	1.0	1.0	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +200		$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX556		ZTX557		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-200		-300		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200		-300		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	$I_E = -100\mu A$
Collector Cut-Off Current	I_{CBO}	-0.1		-0.1		μA	$V_{CB} = -160V$ $V_{CB} = -200V$
Emitter Cut-Off Current	I_{EBO}	-0.1		-0.1		μA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	-0.3		-0.3		V	$I_C = -50mA, I_B = -5mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-1		-1		V	$I_C = -50mA, I_B = -5mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$	-1		-1		V	$I_C = -50mA, V_{CE} = -10V^*$
Static Forward Current Transfer Ratio	h_{FE}	50	300	50	300		$I_C = -10mA, V_{CE} = -10V^*$ $I_C = -50mA, V_{CE} = -10V^*$
Transition Frequency	f_T	75		75		MHz	$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$